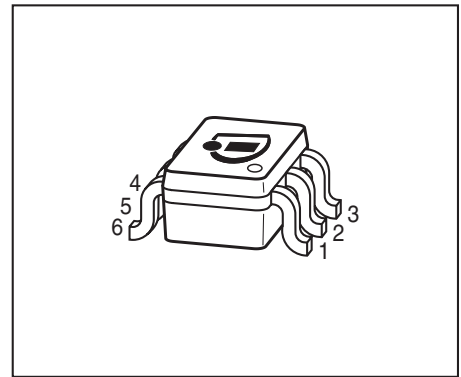
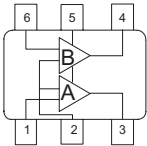


DUAL N-Channel MOSFET Tetrode

- Designed for input stages of 2 band tuners
- Two AGC amplifiers in one single package with on-chip internal switch
- Only one switching line to control both FETs
- Integrated gate protection diodes
- High gain, low noise figure, high AGC-range
- Good cross modulation at gain reduction
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Detailed functional diagram on page 4


BG3430R


ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Package	Pin Configuration						Marking
BG3430R	SOT363	1=G1*	2=S	3=D*	4=D**	5=G2	6=G1**	KNs

* For amp. A; ** for amp. B

180° rotated tape loading orientation available

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	8	V
Continuous drain current	I_D	25	mA
Gate 1/ gate 2-source current	$\pm I_{G1/2SM}$	1	
Gate 1/ gate 2-source voltage	$\pm V_{G1/G2S}$	6	V
Total power dissipation	P_{tot}	200	mW
Storage temperature	T_{stg}	-55 ... 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ¹⁾	R_{thchs}	≤ 280	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

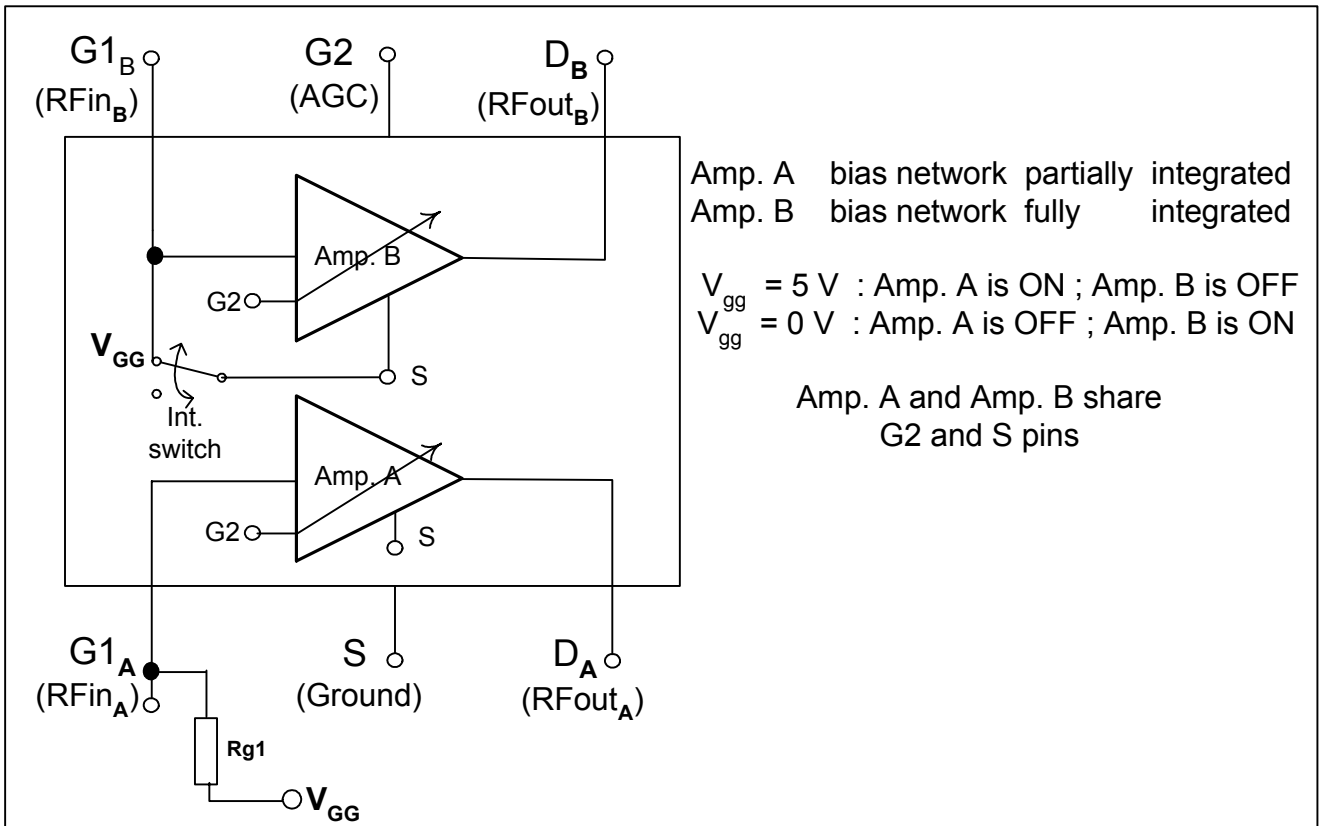
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage $I_D = 100 \mu\text{A}$, $V_{G1S} = 0 \text{ V}$, $V_{G2S} = 0 \text{ V}$	$V_{(BR)DS}$	12	-	-	V
Gate1-source breakdown voltage $+I_{G1S} = 10 \text{ mA}$, $V_{G2S} = 0 \text{ V}$, $V_{DS} = 0 \text{ V}$	$+V_{(BR)G1SS}$	6	-	15	
Gate2-source breakdown voltage $+I_{G2S} = 10 \text{ mA}$, $V_{G1S} = 0 \text{ V}$, $V_{DS} = 0 \text{ V}$	$+V_{(BR)G2SS}$	6	-	15	
Gate1-source leakage current $V_{G1S} = 6 \text{ V}$, $V_{G2S} = 0 \text{ V}$	$+I_{G1SS}$	-	-	5	μA
Gate2-source leakage current $V_{G2S} = 6 \text{ V}$, $V_{G1S} = 0 \text{ V}$, $V_{DS} = 0 \text{ V}$	$+I_{G2SS}$	-	-	50	nA
Drain current $V_{DS} = 5 \text{ V}$, $V_{G1S} = 0 \text{ V}$, $V_{G2S} = 4 \text{ V}$	I_{DSS}	-	-	100	μA
Operating current (selfbiased) $V_{DS} = 5 \text{ V}$, $V_{G2S} = 4 \text{ V}$, amp.B	I_{DSO}	-	13	-	mA
Drain-source current $V_{DS} = 5 \text{ V}$, $V_{G2S} = 4 \text{ V}$, $R_{G1} = 100 \text{ k}\Omega$, amp. A	I_{DSX}	-	13	-	
Gate1-source pinch-off voltage $V_{DS} = 5 \text{ V}$, $V_{G2S} = 4 \text{ V}$, $I_D = 100 \mu\text{A}$	$V_{G1S(p)}$	-	0.5	-	V
Gate2-source pinch-off voltage $V_{DS} = 5 \text{ V}$, $I_D = 100 \mu\text{A}$	$V_{G2S(p)}$	-	0.6	-	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics $V_{DS} = 5\text{V}$, $V_{G2S} = 4\text{V}$, ($I_D = 14\text{ mA}$) (verified by random sampling)					
Forward transconductance	g_{fs}	-	33	-	mS
Gate1 input capacitance $f = 10\text{ MHz}$	C_{g1ss}	-	1.9	-	pF
Output capacitance $f = 10\text{ MHz}$	C_{dss}	-	1.3	-	
Power gain $f = 800\text{ MHz}$ $f = 45\text{ MHz}$	G_p	- -	25 33	- -	dB
Noise figure $f = 800\text{ MHz}$ $f = 45\text{ MHz}$	F	- -	1.3 1	- -	dB
Gain control range $V_{G2S} = 4 \dots 0\text{ V}$, $f = 800\text{ MHz}$	ΔG_p	45	-	-	
Cross-modulation $k=1\%$, $f_w=50\text{MHz}$, $f_{unw}=60\text{MHz}$ AGC = 0 dB AGC = 10 dB AGC = 40 dB	X_{mod}	90 - -	- 93 105	- - -	-

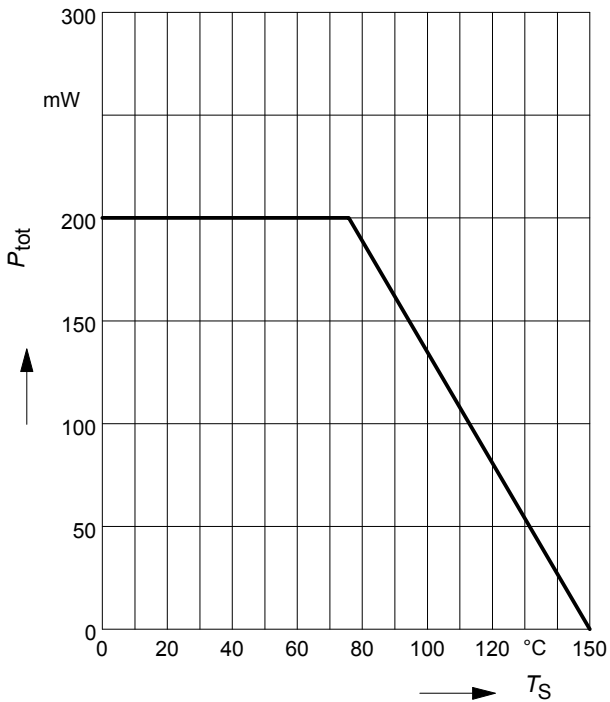
Functional diagram

a) shows pinning of BG3430R.

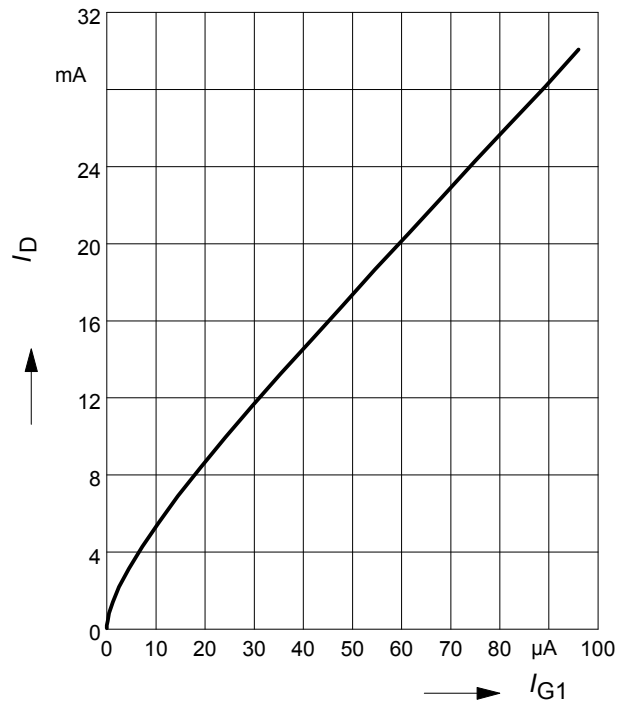


Total power dissipation $P_{tot} = f(T_S)$

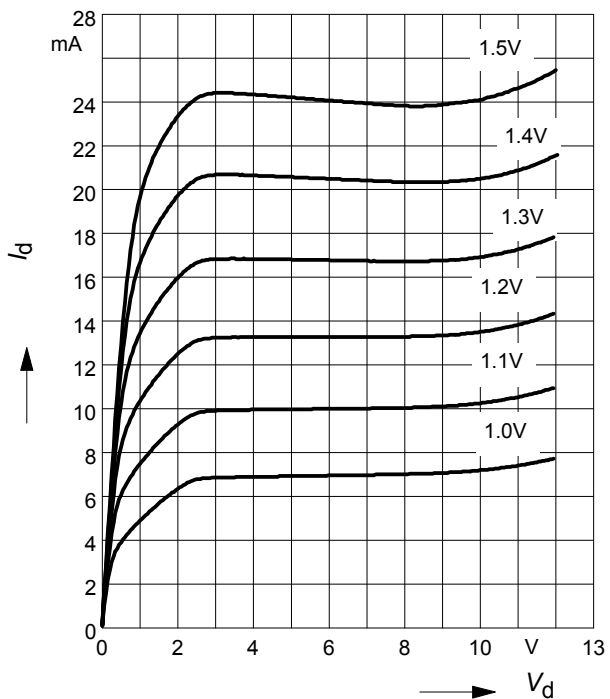
amp. A = amp. B


Drain current $I_D = f(I_{G1})$
 $V_{G2S} = 4V$

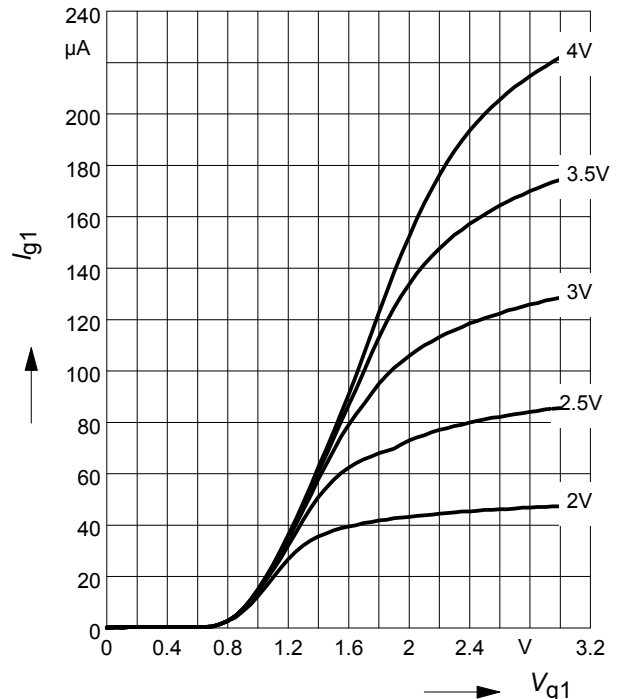
amp. A


Output characteristics $I_D = f(V_{DS})$

amp. A = amp. B

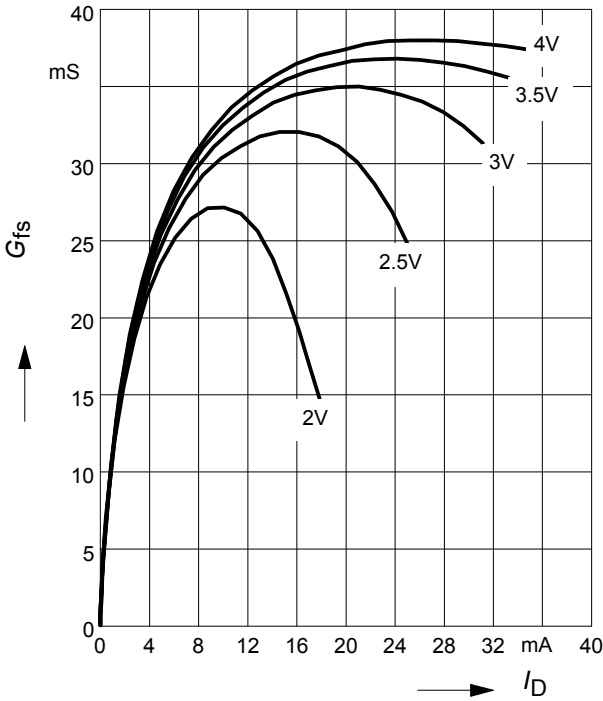

Gate 1 current $I_{G1} = f(V_{G1S})$
 $V_{DS} = 5V, V_{G2S} = \text{Parameter}$

amp. A

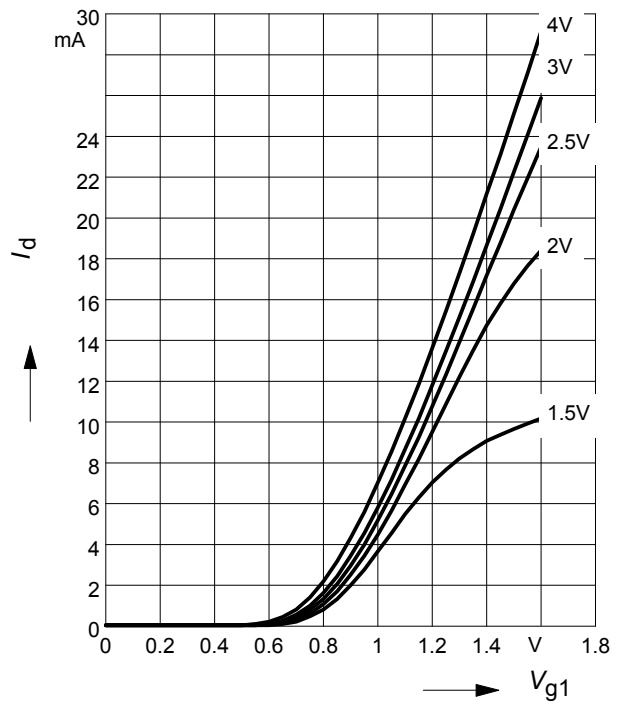


Gate 1 forward transconductance

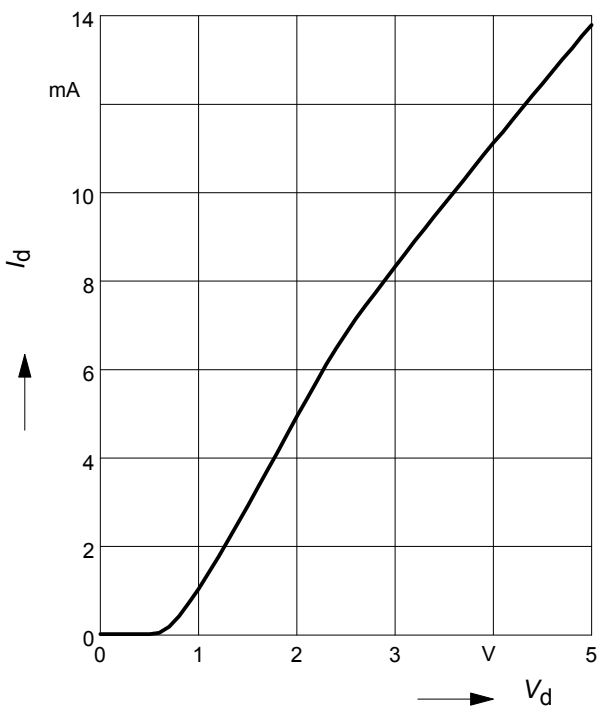
$g_{fs} = f(I_D)$, $V_{DS} = 5V$, $V_{G2S} = \text{Parameter}$
 amp. A = amp. B


Drain current $I_D = f(V_{G1S})$

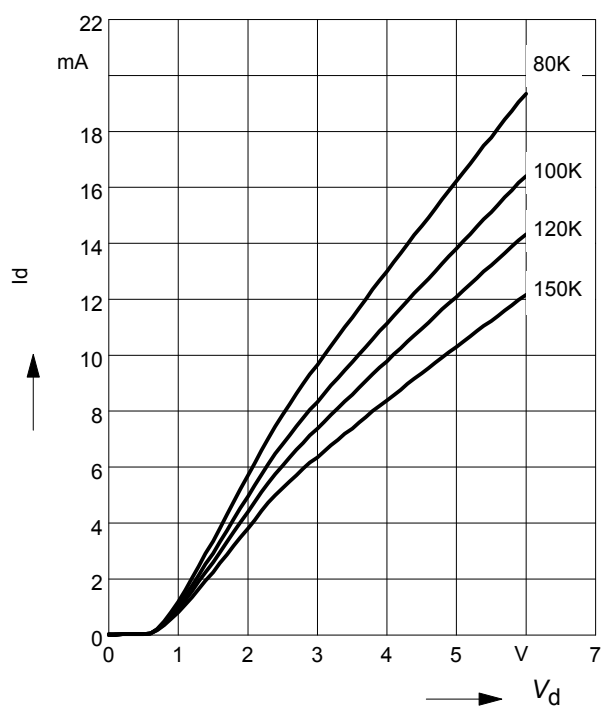
$V_{DS} = 5V$, $V_{G2S} = \text{Parameter}$
 amp. A = amp. B


Drain current $I_D = f(V_{GG})$ amp.A

$V_{DS} = 5V$, $V_{G2S} = 4V$, $R_{G1} = 100k\Omega$
 (connected to V_{GG} , $V_{GG} = \text{gate1 supply voltage}$)

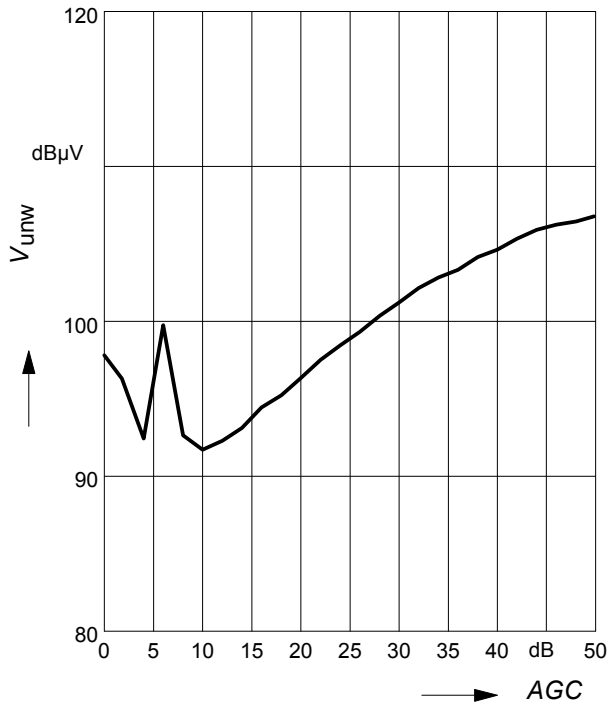

Drain current $I_D = f(V_{GG})$

$V_{G2S} = 4V$, $R_{G1} = \text{Parameter in } k\Omega$
 amp. A

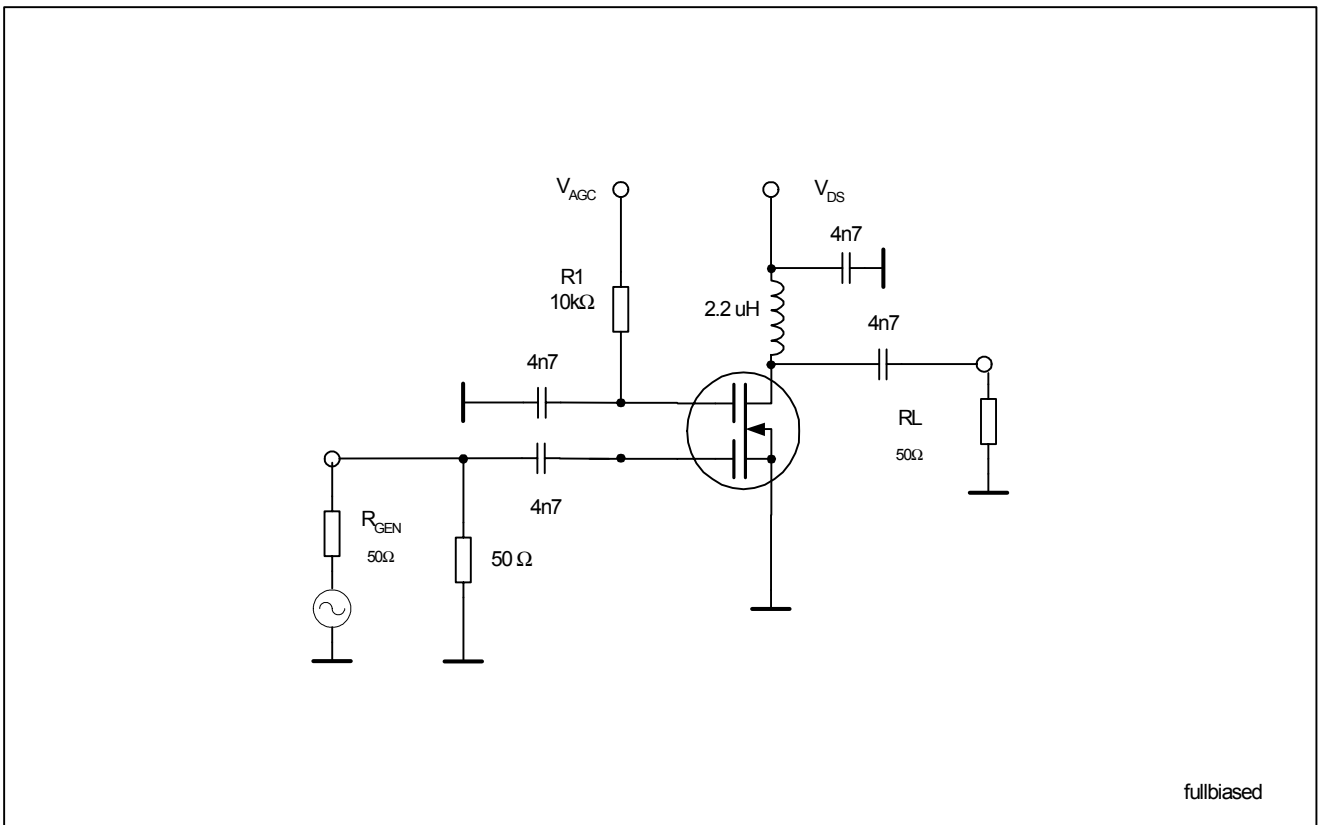
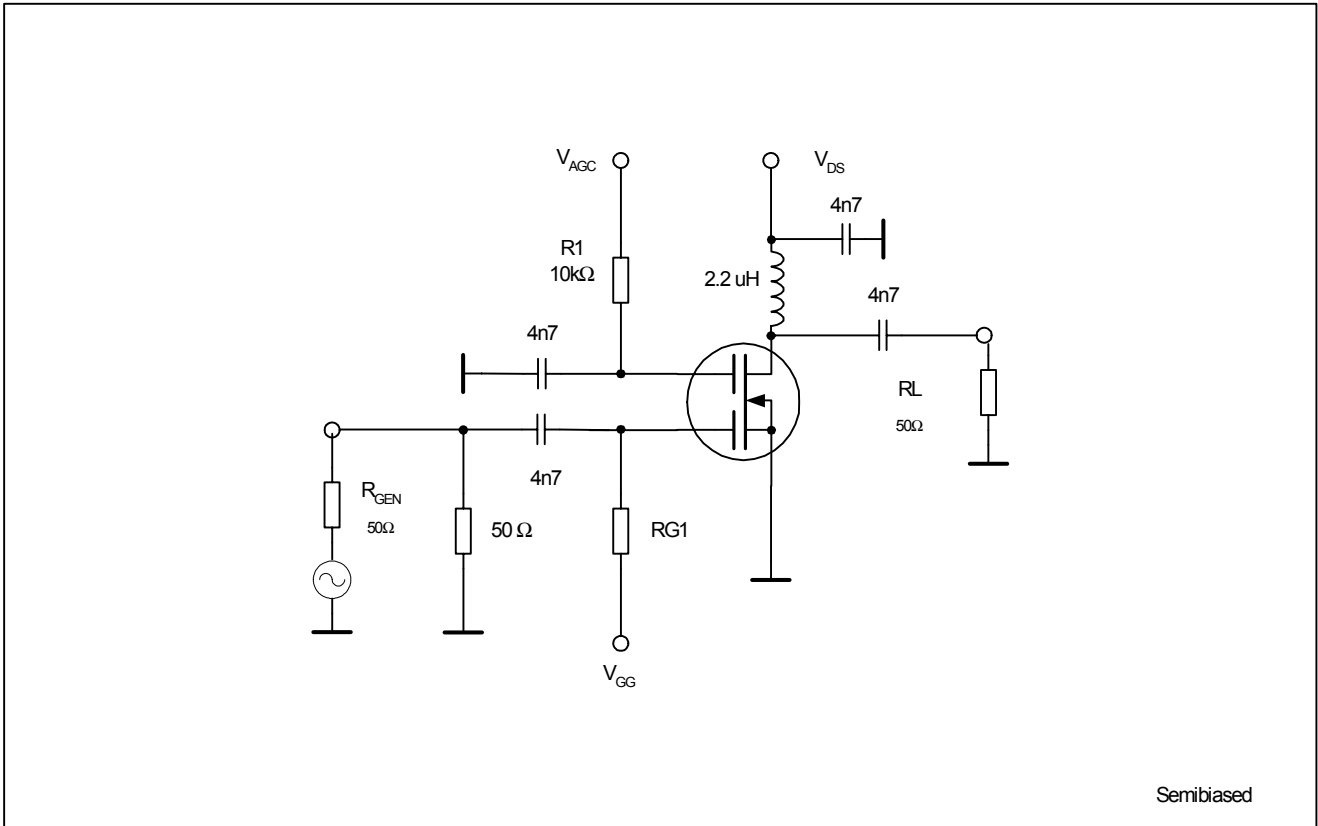


Crossmodulation $V_{unw} = (AGC)$

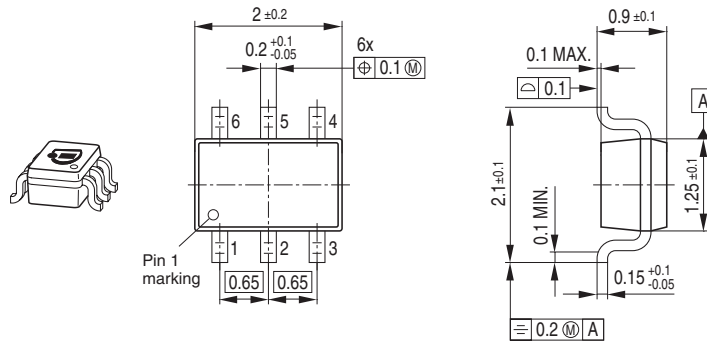
$V_{DS} = 5\text{ V}$, amp. A = amp. B



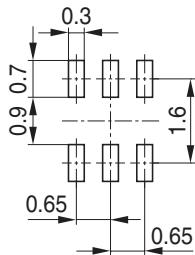
Crossmodulation test circuit



Package Outline

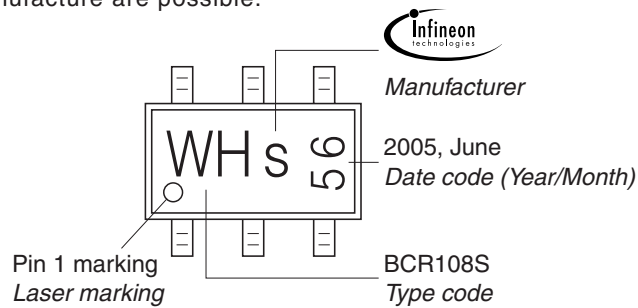


Foot Print



Marking Layout (Example)

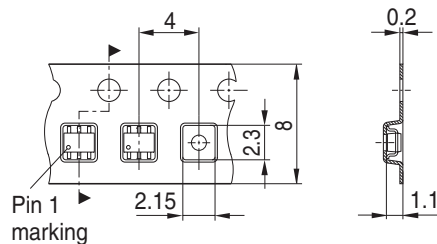
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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